

This listing of claims will replace all prior versions of the claims in the application:

Listing of Claims:

1(Currently amended). A conveyor belt comprising an outer layer and a conveyor-belt base, wherein the outer layer has been produced via plasma coating, and has an oxygen content at its surface of about 10 to about 30 atom %, as determined by X-ray photoelectron spectroscopy.

2(Previously presented). The conveyor belt as claimed in claim 1, wherein the outer layer comprises an underlayer produced via plasma coating, and adheres by means of this underlayer to the conveyor-belt base.

3(Previously presented). The conveyor belt as claimed in claim 1, wherein the thickness of the outer layer is in the range from 0.005 to 10 μm .

4(Previously presented). The conveyor belt as claimed in claim 2, wherein the thickness of the underlayer is from 0.005 to 10 μm .

5(Currently amended). A process for production of an outer layer on a conveyor-belt base comprising exposing the conveyor-belt base, in the presence of a gaseous monomer capable of excitation in a plasma, the conveyor-belt base is exposed to a plasma in such a way that the gaseous monomer is excited generated via microwaves of 1 to 10 GHz for purposes of plasma coating of the conveyor-belt base, wherein either the exposure is done with simultaneous addition of O₂ as an auxiliary gas, or the process is an air-to-air process.

6(Currently amended). An air-to-air process for coating of a conveyor-belt base with an

outer layer which comprises an underlayer, characterized in that the conveyor-belt base is exposed, in the presence of a gaseous monomer capable of excitation in a first plasma, ~~the conveyor-belt base is exposed~~ to a first plasma generated via microwaves of 1 to 10 GHz in such a way that the first gaseous monomer is excited for purposes of forming an underlayer on the conveyor-belt base; and then either

- a) in the presence of said first monomer, the underlayer is exposed to a second plasma generated via microwaves of 1 to 10 GHz different from the first plasma in such a way that the first monomer is excited for purposes of plasma coating of the underlayer,
or
- (b) in the presence of a second gaseous monomer different from the first monomer and capable of excitation in a plasma, the underlayer is exposed to a plasma generated via microwaves of 1 to 10 GHz in such a way that the second monomer is excited for purposes of plasma coating of the underlayer.

7(Canceled).

8(Currently amended). The process as claimed in claim 5, wherein the monomer(s) ~~has/have been is/are~~ selected from: ethene; its derivatives substituted with halogen and/or substituted with trifluoromethyl, or its derivatives substituted with π -electron-withdrawing groups; the unbranched or branched alkanes having from 2 to 12 carbon atoms; the cyclic (C₄-C₇) alkanes; the halogenated alkanes, where the halogen atoms have been selected from fluorine and chlorine and where the total calculated from the number of carbon atoms plus the number of fluorine atoms plus twice the number of chlorine atoms is at most 12; the silicon-containing monomers, in particular the (C₃-C₁₀) silanes, (C₄-C₈) siloxanes, or (C₄-C₈) silazanes; acetylene and its derivatives substituted with unbranched or branched, optionally fluorine-substituted alkyl substituents, where the total number of all of the carbon atoms plus all of the fluorine atoms is at most 12; and the iso- or heterocyclic unsubstituted or (C₁-C₄)-alkyl- or (C₂-C₄)-alkenyl-substituted or halogen-

substituted aromatics, where the total calculated from the number of carbon atoms plus the number of oxygen atoms plus the number of nitrogen atoms plus the number of fluorine atoms plus twice the number of sulfur atoms plus twice the number of chlorine atoms is at most 12.

9(Original). The process as claimed in claim 8, characterized in that the monomer(s) is/are selected from tetrafluoroethylene, 1,2-difluoroethylene, acetylene, or hexamethyldisiloxane (HMDSO).

10(Canceled).

11(Previously presented). The conveyor belt as claimed in claim 2, wherein the thickness of the outer layer is in the range from 0.005 to 10 μm .

12(Canceled).

13(Currently amended). The process as claimed in claim 6, wherein the monomer(s) has/have been is/are selected from: ethene; its derivatives substituted with halogen and/or substituted with trifluoromethyl, or its derivatives substituted with π -electron-withdrawing groups; the unbranched or branched alkanes having from 2 to 12 carbon atoms; the cyclic (C₄-C₇) alkanes; the halogenated alkanes, where the halogen atoms have been selected from fluorine and chlorine and where the total calculated from the number of carbon atoms plus the number of fluorine atoms plus twice the number of chlorine atoms is at most 12; the silicon-containing monomers, in particular the (C₃-C₁₀) silanes, (C₄-C₈) siloxanes, or (C₄-C₈) silazanes; acetylene and its derivatives substituted with unbranched or branched, optionally fluorine-substituted alkyl substituents, where the total number of all of the carbon atoms plus all of the fluorine atoms is at most 12; and the iso- or heterocyclic unsubstituted or (C₁-C₄)-alkyl- or (C₂-C₄)-alkenyl-substituted or halogen-

substituted aromatics, where the total calculated from the number of carbon atoms plus the number of oxygen atoms plus the number of nitrogen atoms plus the number of fluorine atoms plus twice the number of sulfur atoms plus twice the number of chlorine atoms is at most 12.

14(Currently amended). The process as claimed in claim 7, wherein the monomer(s) ~~has/have been is/are~~ selected from: ethene; its derivatives substituted with halogen and/or substituted with trifluoromethyl, or its derivatives substituted with π -electron-withdrawing groups; the unbranched or branched alkanes having from 2 to 12 carbon atoms; the cyclic (C₄-C₇) alkanes; the halogenated alkanes, where the halogen atoms have been selected from fluorine and chlorine and where the total calculated from the number of carbon atoms plus the number of fluorine atoms plus twice the number of chlorine atoms is at most 12; the silicon-containing monomers, in particular the (C₃-C₁₀) silanes, (C₄-C₈) siloxanes, or (C₄-C₈) silazanes; acetylene and its derivatives substituted with unbranched or branched, optionally fluorine-substituted alkyl substituents, where the total number of all of the carbon atoms plus all of the fluorine atoms is at most 12; and the iso- or heterocyclic unsubstituted or (C₁-C₄)-alkyl- or (C₂-C₄)-alkenyl-substituted or halogen-substituted aromatics, where the total calculated from the number of carbon atoms plus the number of oxygen atoms plus the number of nitrogen atoms plus the number of fluorine atoms plus twice the number of sulfur atoms plus twice the number of chlorine atoms is at most 12.